

ABSTRACT

SEMICONDUCTOR STRUCTURES AND A METHOD OF
MANUFACTURING SEMICONDUCTOR STRUCTURES

5 In a semiconductor buried heterostructure laser, having a
mesa 2, 3, 4 and confinement layers 5, 6, 7 on a substrate
12, at least the lowermost of the confinement layers 5, 6,
7 is substantially planar up to the mesa. This is
achieved by MOVPE growth of InP against lateral surfaces
of the mesa 2, 3, 4 which are defined by distinct
10 crystallographic planes of the material of the mesa. In
particular (111) B InP planes are used. The laser is
particularly for use in the field of optical
communications.

15

20

25

30 This Sheet Has Been Replaced

